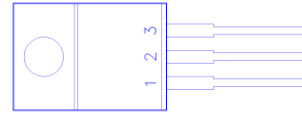
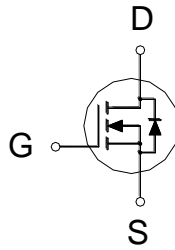


**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
60V	10m $\Omega$	61A



1: GATE  
2: DRAIN  
3: SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>2</sup>	$T_C = 25^\circ\text{C}$	$I_D$	61	A
	$T_C = 100^\circ\text{C}$		39	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	150	
Avalanche Current		$I_{AS}$	39	
Avalanche Energy	$L = 0.1\text{mH}$	$E_{AS}$	77	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	83	W
	$T_C = 100^\circ\text{C}$		33	
Junction & Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	$^\circ\text{C} / \text{W}$
Junction-to-Case	$R_{\theta JC}$		1.5	

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Package limitation current is 30A.

**ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.3	1.7	2.3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
		$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$			10	
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 4.5\text{V}, I_D = 20\text{A}$		8.2	13	m $\Omega$
		$V_{GS} = 10\text{V}, I_D = 20\text{A}$		6.8	10	

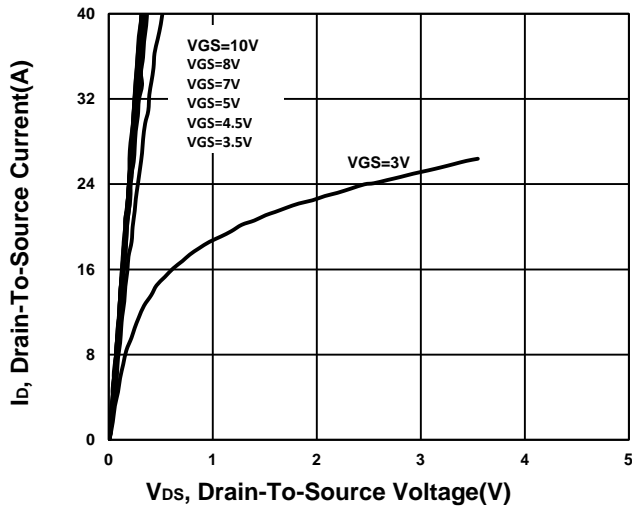
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 10V, I_D = 20A$		60		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		1853		pF
Output Capacitance	$C_{oss}$			224		
Reverse Transfer Capacitance	$C_{rss}$			142		
Gate Resistance	$R_g$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$		0.8		$\Omega$
Total Gate Charge <sup>2</sup>	$Q_{g(VGS=10V)}$	$V_{DS} = 30V, I_D = 20A$		42.2		nC
	$Q_{g(VGS=4.5V)}$			23.1		
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			5.6		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			12.8		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$		$V_{DS} = 30V, I_D \cong 20A,$ $V_{GS} = 10V, R_{GEN} = 6\Omega$		30	
Rise Time <sup>2</sup>	$t_r$			29		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			50		
Fall Time <sup>2</sup>	$t_f$			33		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 ° C)</b>						
Continuous Current <sup>3</sup>	$I_S$			61		A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = 20A, V_{GS} = 0V$		1.3		V
Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20A, di/dt = 100A/\mu s$		29		nS
Diode Reverse Recovery Charge	$Q_{rr}$			27		uC

<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

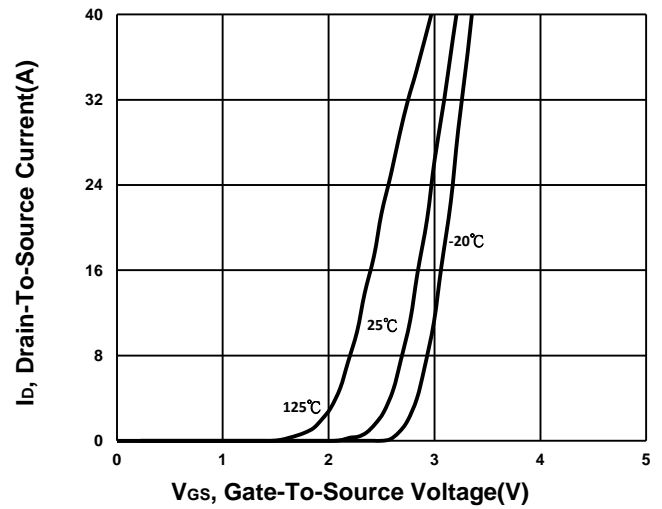
<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Package limitation current is 30A

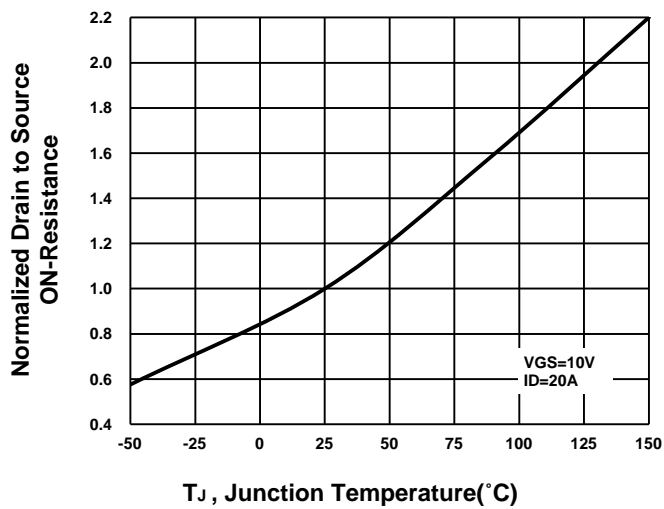
**Output Characteristics**



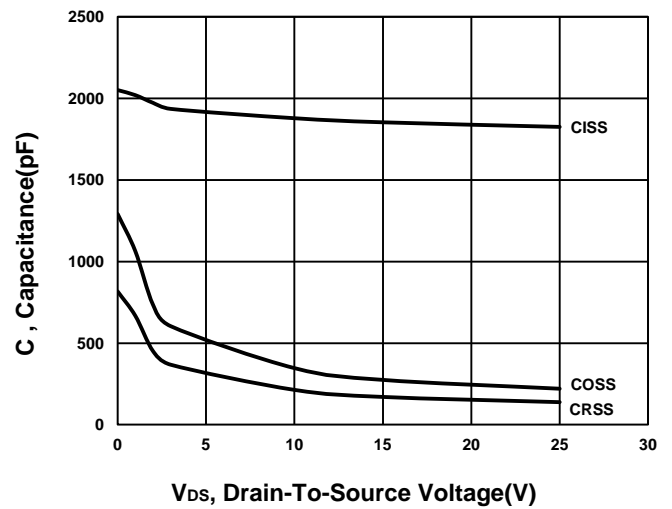
**Transfer Characteristics**



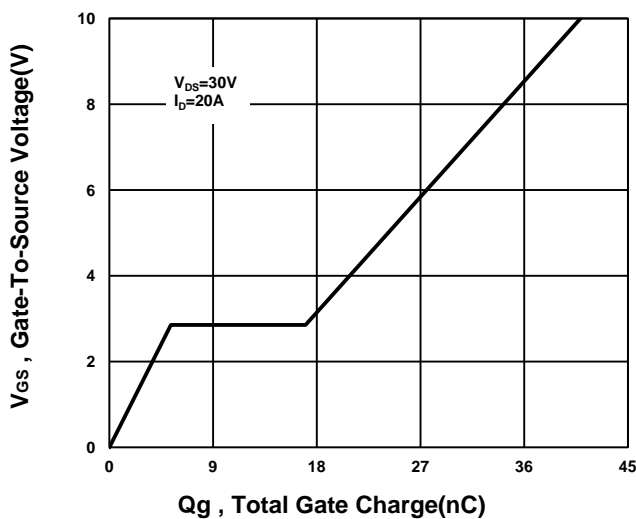
**On-Resistance VS Temperature**



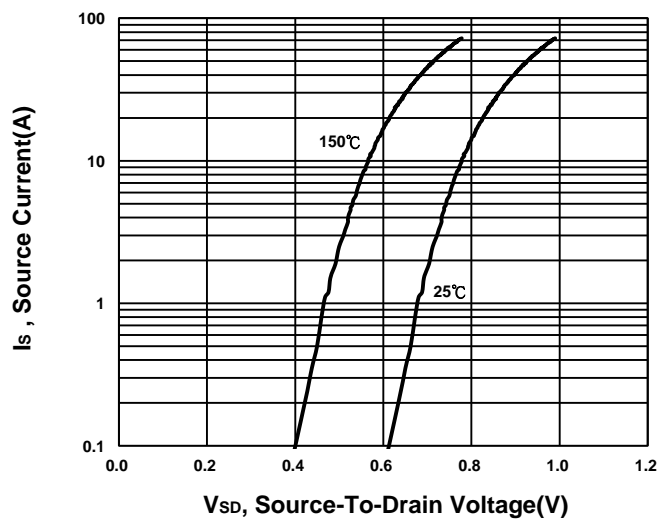
**Capacitance Characteristic**



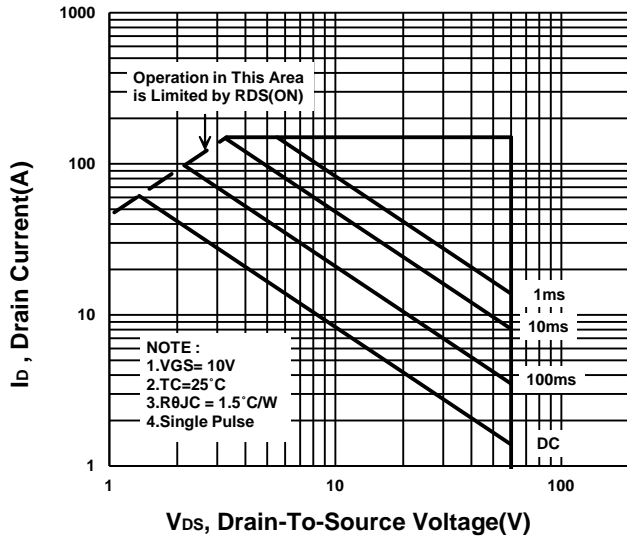
**Gate charge Characteristics**



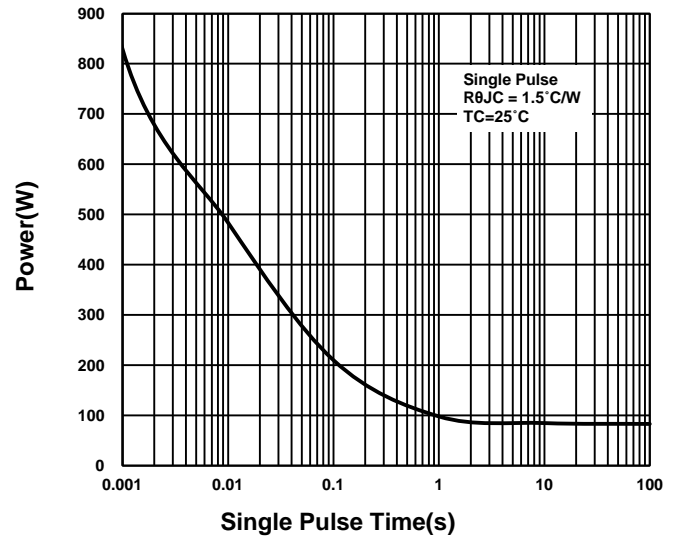
**Source-Drain Diode Forward Voltage**



**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**

